MJE13005D

Preliminary

NPN SILICON TRANSISTOR

HIGH VOLTAGE FAST-SWITCHING NPN POWER **TRANSISTOR**

DESCRIPTION

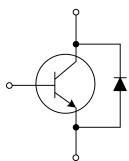
The UTC MJE13005D is a high voltage fast-switching NPN power transistor. It is characterized by high breakdown voltage, high current capability, high switching speed and high reliability.

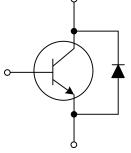
The UTC MJE13005D is intended to be used in energy-saving light, electronic ballast, high frequency switching power supply, high frequency power transform or common power amplifier, etc.

FEATURES

- * High Breakdown Voltage
- * High Current Capability
- * High Switching Speed
- * High Reliability
- * RoHS-Compliant Product

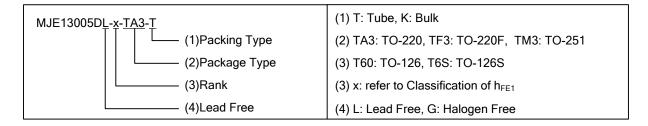


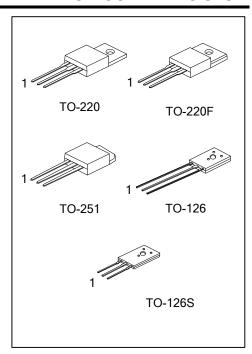




ORDERING INFORMATION

Ordering	Dookogo	Pin Assignment			Dooking		
Lead Free	Halogen Free	Package	1	2	3	Packing	
MJE13005DL-x-TA3-T	MJE13005DG-x-TA3-T	TO-220	В	С	Е	Tube	
MJE13005DL-x-TF3-T	MJE13005DG-x-TF3-T	TO-220F	В	С	Е	Tube	
MJE13005DL-x-TM3-T	MJE13005DG-x-TM3-T	TO-251	В	С	Е	Tube	
MJE13005DL-x-T60-K	MJE13005DG-x-T60-K	TO-126	В	С	Е	Bulk	
MJE13005DL-x-T6S-K	MJE13005DG-x-T6S-K	TO-126S	В	С	Е	Bulk	





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■ ABSOLUTE MAXIMUM RATING (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATING	UNIT
Collector- Emitter Voltage (V _{BE} =0)		V_{CES}	700	V
Collector-Emitter Voltage (I _B =0)		V_{CEO}	400	V
Emitter-Base Voltage		V_{EBO}	9	V
Collector Current	DC	Ic	4	Α
	Pulse	I _{CP}	8	Α
Base Current	DC	I _B	2	Α
	Pulse	I _{BP}	4	Α
Power Dissipation	TO-220/TO-220F		75	
	TO-251	P_{D}	50	W
	TO-126/TO-126S		45	
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle < 10%.

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT	
	TO-220/TO-220F		62.5		
Junction to Ambient	TO-251	θ_{JA}	110	°C/W	
	TO-126/TO-126S		89		
	TO-220/TO-220F		1.67		
Junction to Case	TO-251	θ_{JC}	2.5	°C/W	
	TO-126/TO-126S		2.78		

■ ELECTRICAL CHARACTERISTICS

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Collector-Emitter Breakdown Voltage		BV _{CEO}	I _C =10mA, I _B =0	400			V	
Collector -Base Breakdown Voltage		BV_CBO	I _C =1mA, I _B =0	700			V	
Emitter-Base Breakdo	wn Voltage	BV_{EBO}	I _E =1mA, I _C =0	9			V	
Collect Cut-off Current	İ	I _{CBO}	V _{CB} =700V, I _E =0			100	μΑ	
Collect Cut-off Current		I _{CEO}	V _{CE} =400V,I _B =0			50	μΑ	
Emitter Cut-off Current		I _{EBO}	V _{EB} =9V, I _C =0			10	μA	
DC Current Gain		h _{FE1}	V _{CE} =5V, I _C =500mA	15		50		
		h _{FE2}	V _{CE} =5V, I _C =2A	5				
Collector-Emitter Saturation Voltage			I _C =1A, I _B =0.2A			0.5	V	
		V _{CE}	I _C =2A, I _B =0.5A			0.6		
			I _C =4A, I _B =1A			1		
			I _C =2A, I _B =0.5A, T _C =100°C			1		
Base-Emitter Saturation Voltage		$V_{BE(SAT)}$	I _C =2A, I _B =0.5A			1.6	V	
Resistive Load	Fall Time	t_{F}	V 04V 1 04 1 0 44			0.7	μs	
	Storage Time	ts	V_{CC} =24V, I_C =2A, I_{B1} =- I_{B2} =0.4A			4	μs	
Current Gain Bandwidth Product		f_T	V _{CE} =10V, I _C =0.5A	4			MH_Z	
Diode Forward Voltage		V_{F}	I _F =1A			1.5	V	

CLASSIFICATION OF h_{FE1}

RANK	Α	В	С	D	E
RANGE	15 ~ 20	20 ~ 25	25 ~ 30	30 ~ 40	40 ~ 50

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